



**100mW STEREO HEADPHONE AMPLIFIER**

- Operating from **V<sub>CC</sub>=2V to 5.5V**
- 100mW into 16Ω at 5V
- 38mW into 16Ω at 3.3V
- 11.5mW into 16Ω at 2V
- Switch ON/OFF click reduction circuitry
- High Power Supply Rejection Ratio: 85dB at 5V
- High Signal-to-Noise ratio: 110dB(A) at 5V
- High Crosstalk immunity: 100dB (F=1kHz)
- Rail to Rail input and output
- Unity-Gain Stable
- Available in **SO8, MiniSO8 & DFN8**

**DESCRIPTION**

The TS482 is a dual audio power amplifier able to drive a 16 or 32Ω stereo headset down to low voltages.

It's delivering up to 100mW per channel (into 16Ω loads) of continuous average power with 0.1% THD+N from a 5V power supply.

The unity gain stable TS482 can be configured by external gain-setting resistors.

**APPLICATIONS**

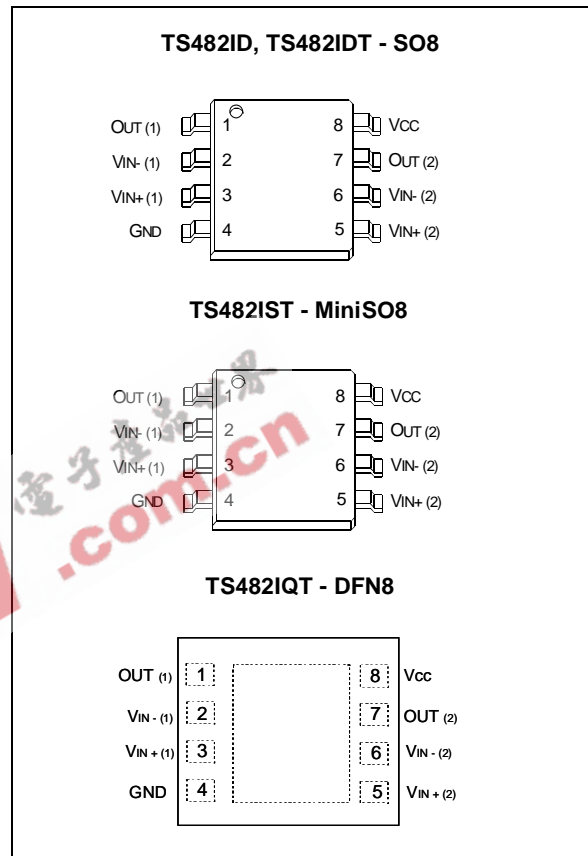
- Stereo Headphone Amplifier
- Optical Storage
- Computer Motherboard
- PDA, organizers & Notebook computers
- High end TV, Set Top Box, DVD Players
- Sound Cards

**ORDER CODE**

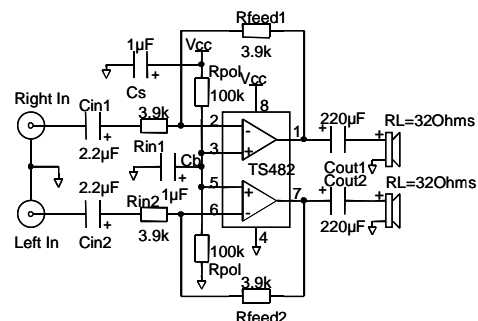
Part Number	Temperature Range	Package			Marking
		D	S	Q	
TS482ID/DT	-40, +85°C	•			482I
TS482IST			•		
TS482IQT				•	

MiniSO & DFN only available in Tape & Reel with T suffix, SO is available in Tube (D) and in Tape & Reel (DT)

**PIN CONNECTIONS (top view)**



**TYPICAL APPLICATION SCHEMATIC**



**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply voltage <sup>1)</sup>	6	V
V <sub>i</sub>	Input Voltage	-0.3 to V <sub>CC</sub> +0.3	V
T <sub>oper</sub>	Operating Free Air Temperature Range	-40 to + 85	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>j</sub>	Maximum Junction Temperature	150	°C
R <sub>thja</sub>	Thermal Resistance Junction to Ambient SO8 MiniSO8 DFN8	175 215 70	°C/W
Pd	Power Dissipation <sup>2)</sup> SO8 MiniSO8 DFN8	0.71 0.58 1.79	W
ESD	Human Body Model (pin to pin)	2	kV
ESD	Machine Model - 220pF - 240pF (pin to pin)	200	V
Latch-up	Latch-up Immunity (All pins)	200	mA
	Lead Temperature (soldering, 10sec)	250	°C
	Output Short-Circuit Duration	see note <sup>3)</sup>	

1. All voltages values are measured with respect to the ground pin.

2. Pd has been calculated with Tamb = 25°C, Tjunction = 150°C.

3. Attention must be paid to continuous power dissipation. Exposure of the IC to a short circuit on one or two amplifiers simultaneously can cause excessive heating and the destruction of the device.

**OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	2 to 5.5	V
R <sub>L</sub>	Load Resistor	>= 16	Ω
C <sub>L</sub>	Load Capacitor R <sub>L</sub> = 16 to 100Ω R <sub>L</sub> > 100Ω	400 100	pF
V <sub>ICM</sub>	Common Mode Input Voltage Range	G <sub>ND</sub> to V <sub>CC</sub>	V
R <sub>THJA</sub>	Thermal Resistance Junction to Ambient SO8 MiniSO8 DFN8 <sup>1)</sup>	150 190 41	°C/W

1. When mounted on a 4-layer PCB.

Components	Functional Description
Rin	Inverting input resistor which sets the closed loop gain in conjunction with Rfeed. This resistor also forms a high pass filter with Cin (fc = 1 / (2 x Pi x Rin x Cin))
Cin	Input coupling capacitor which blocks the DC voltage at the amplifier input terminal
Rfeed	Feed back resistor which sets the closed loop gain in conjunction with Rin
Cs	Supply Bypass capacitor which provides power supply filtering
Cb	Bypass capacitor which provides half supply filtering
Cout	Output coupling capacitor which blocks the DC voltage at the load input terminal This capacitor also forms a high pass filter with RL (fc = 1 / (2 x Pi x RL x Cout))
Rpol	These 2 resistors form a voltage divider which provide a DC biasing voltage (Vcc/2) for the 2 amplifiers.
Av	Closed loop gain = -Rfeed / Rin

**ELECTRICAL CHARACTERISTICS** $V_{CC} = +5V$ ,  $GND = 0V$ ,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit
$I_{CC}$	Supply Current No input signal, no load		5.5	7.2	mA
$V_{IO}$	Input Offset Voltage ( $V_{ICM} = V_{CC}/2$ )		1	5	mV
$I_{IB}$	Input Bias Current ( $V_{ICM} = V_{CC}/2$ )		200	500	nA
$P_O$	Output Power THD+N = 0.1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 0.1% Max, F = 1kHz, $R_L = 16\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 16\Omega$	60 95	65 67.5 100 107		mW
THD + N	Total Harmonic Distortion + Noise ( $A_v=-1$ ) <sup>1)</sup> $R_L = 32\Omega$ , $P_{out} = 60mW$ , $20Hz \leq F \leq 20kHz$ $R_L = 16\Omega$ , $P_{out} = 90mW$ , $20Hz \leq F \leq 20kHz$		0.03 0.03		%
PSRR	Power Supply Rejection Ratio ( $A_v=1$ ), inputs floating F = 100Hz, Vripple = 100mVpp		85		dB
$I_O$	Max Output Current THD +N < 1%, $R_L = 16\Omega$ connected between out and $V_{CC}/2$	106	120		mA
$V_O$	Output Swing $V_{OL} : R_L = 32\Omega$ $V_{OH} : R_L = 32\Omega$ $V_{OL} : R_L = 16\Omega$ $V_{OH} : R_L = 16\Omega$	4.45 4.2	0.4 4.6 0.55 4.4	0.48 0.65	V
SNR	Signal-to-Noise Ratio (Filter Type A, $A_v=-1$ ) ( $R_L = 32\Omega$ , THD +N < 0.2%, $20Hz \leq F \leq 20kHz$ )	95	110		dB
Crosstalk	Channel Separation, $R_L = 32\Omega$ F = 1kHz F = 20Hz to 20kHz Channel Separation, $R_L = 16\Omega$ F = 1kHz F = 20Hz to 20kHz		100 80 100 80		dB
$C_I$	Input Capacitance		1		pF
GBP	Gain Bandwidth Product ( $R_L = 32\Omega$ )	1.35	2.2		MHz
SR	Slew Rate, Unity Gain Inverting ( $R_L = 16\Omega$ )	0.45	0.7		V/ $\mu$ s

1. Fig. 68 to 79 show dispersion of these parameters.

**ELECTRICAL CHARACTERISTICS**
 $V_{CC} = +3.3V$ ,  $GND = 0V$ ,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified) <sup>2)</sup>

Symbol	Parameter	Min.	Typ.	Max.	Unit
$I_{CC}$	Supply Current No input signal, no load		5.3	7.2	mA
$V_{IO}$	Input Offset Voltage ( $V_{ICM} = V_{CC}/2$ )		1	5	mV
$I_{IB}$	Input Bias Current ( $V_{ICM} = V_{CC}/2$ )		200	500	nA
$P_O$	Output Power THD+N = 0.1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 0.1% Max, F = 1kHz, $R_L = 16\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 16\Omega$	23 36	27 28 38 42		mW
THD + N	Total Harmonic Distortion + Noise ( $A_v=-1$ ) <sup>1)</sup> $R_L = 32\Omega$ , $P_{out} = 16mW$ , $20Hz \leq F \leq 20kHz$ $R_L = 16\Omega$ , $P_{out} = 35mW$ , $20Hz \leq F \leq 20kHz$		0.03 0.03		%
PSRR	Power Supply Rejection Ratio ( $A_v=1$ ), inputs floating F = 100Hz, Vripple = 100mVpp		80		dB
$I_O$	Max Output Current THD +N < 1%, $R_L = 16\Omega$ connected between out and $V_{CC}/2$	64	75		mA
$V_O$	Output Swing $V_{OL} : R_L = 32\Omega$ $V_{OH} : R_L = 32\Omega$ $V_{OL} : R_L = 16\Omega$ $V_{OH} : R_L = 16\Omega$	2.85 2.68	0.3 3 0.45 2.85	0.38 0.52	V
SNR	Signal-to-Noise Ratio (Filter Type A, $A_v=-1$ ) ( $R_L = 32\Omega$ , THD +N < 0.2%, $20Hz \leq F \leq 20kHz$ )	92	107		dB
Crosstalk	Channel Separation, $R_L = 32\Omega$ F = 1kHz F = 20Hz to 20kHz Channel Separation, $R_L = 16\Omega$ F = 1kHz F = 20Hz to 20kHz		100 80 100 80		dB
$C_I$	Input Capacitance		1		pF
GBP	Gain Bandwidth Product ( $R_L = 32\Omega$ )	1.2	2		MHz
SR	Slew Rate, Unity Gain Inverting ( $R_L = 16\Omega$ )	0.45	0.7		V/ $\mu$ s

1. Fig. 68 to 79 show dispersion of these parameters.

2. All electrical values are guaranteed with correlation measurements at 2V and 5V

**ELECTRICAL CHARACTERISTICS**
 $V_{CC} = +2.5V$ ,  $GND = 0V$ ,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified) <sup>2)</sup>

Symbol	Parameter	Min.	Typ.	Max.	Unit
$I_{CC}$	Supply Current No input signal, no load		5.1	7.2	mA
$V_{IO}$	Input Offset Voltage ( $V_{ICM} = V_{CC}/2$ )		1	5	mV
$I_{IB}$	Input Bias Current ( $V_{ICM} = V_{CC}/2$ )		200	500	nA
$P_O$	Output Power THD+N = 0.1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 0.1% Max, F = 1kHz, $R_L = 16\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 16\Omega$	12.5 17.5	13.5 14.5 20.5 22		mW
THD + N	Total Harmonic Distortion + Noise ( $A_v=-1$ ) <sup>1)</sup> $R_L = 32\Omega$ , $P_{out} = 10mW$ , $20Hz \leq F \leq 20kHz$ $R_L = 16\Omega$ , $P_{out} = 16mW$ , $20Hz \leq F \leq 20kHz$		0.03 0.03		%
PSRR	Power Supply Rejection Ratio ( $A_v=1$ ), inputs floating F = 100Hz, Vripple = 100mVpp		75		dB
$I_O$	Max Output Current THD + N < 1%, $R_L = 16\Omega$ connected between out and $V_{CC}/2$	45	56		mA
$V_O$	Output Swing $V_{OL} : R_L = 32\Omega$ $V_{OH} : R_L = 32\Omega$ $V_{OL} : R_L = 16\Omega$ $V_{OH} : R_L = 16\Omega$	2.14 1.97	0.25 2.25 0.35 2.15	0.325 0.45	V
SNR	Signal-to-Noise Ratio (Filter Type A, $A_v=-1$ ) ( $R_L = 32\Omega$ , THD + N < 0.2%, $20Hz \leq F \leq 20kHz$ )	89	102		dB
Crosstalk	Channel Separation, $R_L = 32\Omega$ F = 1kHz F = 20Hz to 20kHz Channel Separation, $R_L = 16\Omega$ F = 1kHz F = 20Hz to 20kHz		100 80 100 80		dB
$C_I$	Input Capacitance		1		pF
GBP	Gain Bandwidth Product ( $R_L = 32\Omega$ )	1.2	2		MHz
SR	Slew Rate, Unity Gain Inverting ( $R_L = 16\Omega$ )	0.45	0.7		V/ $\mu$ s

1. Fig. 68 to 79 show dispersion of these parameters.

2. All electrical values are guaranteed with correlation measurements at 2V and 5V

**ELECTRICAL CHARACTERISTICS** $V_{CC} = +2V$ ,  $GND = 0V$ ,  $T_{amb} = 25^{\circ}C$  (unless otherwise specified)

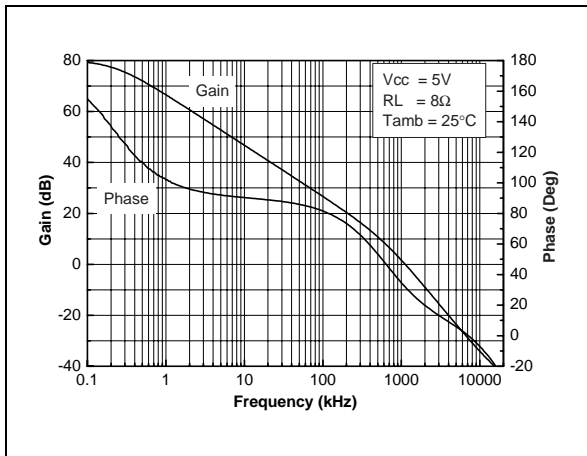
Symbol	Parameter	Min.	Typ.	Max.	Unit
$I_{CC}$	Supply Current No input signal, no load		5	7.2	mA
$V_{IO}$	Input Offset Voltage ( $V_{ICM} = V_{CC}/2$ )		1	5	mV
$I_{IB}$	Input Bias Current ( $V_{ICM} = V_{CC}/2$ )		200	500	nA
$P_O$	Output Power THD+N = 0.1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 32\Omega$ THD+N = 0.1% Max, F = 1kHz, $R_L = 16\Omega$ THD+N = 1% Max, F = 1kHz, $R_L = 16\Omega$	7 9.5	8 9 11.5 13		mW
THD + N	Total Harmonic Distortion + Noise ( $A_v=-1$ ) <sup>1)</sup> $R_L = 32\Omega$ , $P_{out} = 6.5mW$ , $20Hz \leq F \leq 20kHz$ $R_L = 16\Omega$ , $P_{out} = 8mW$ , $20Hz \leq F \leq 20kHz$		0.02 0.025		%
PSRR	Power Supply Rejection Ratio ( $A_v=1$ ), inputs floating F = 100Hz, Vripple = 100mVpp		75		dB
$I_O$	Max Output Current THD +N < 1%, $R_L = 16\Omega$ connected between out and $V_{CC}/2$	33	41.5		mA
$V_O$	Output Swing $V_{OL} : R_L = 32\Omega$ $V_{OH} : R_L = 32\Omega$ $V_{OL} : R_L = 16\Omega$ $V_{OH} : R_L = 16\Omega$	1.67 1.53	0.24 1.73 0.33 1.63	0.295 0.41	V
SNR	Signal-to-Noise Ratio (Filter Type A, $A_v=-1$ ) ( $R_L = 32\Omega$ , THD +N < 0.2%, $20Hz \leq F \leq 20kHz$ )	88	101		dB
Crosstalk	Channel Separation, $R_L = 32\Omega$ F = 1kHz F = 20Hz to 20kHz Channel Separation, $R_L = 16\Omega$ F = 1kHz F = 20Hz to 20kHz		100 80 100 80		dB
$C_I$	Input Capacitance		1		pF
GBP	Gain Bandwidth Product ( $R_L = 32\Omega$ )	1.2	2		MHz
SR	Slew Rate, Unity Gain Inverting ( $R_L = 16\Omega$ )	0.42	0.65		V/ $\mu$ s

1. Fig. 68 to 79 show dispersion of these parameters.

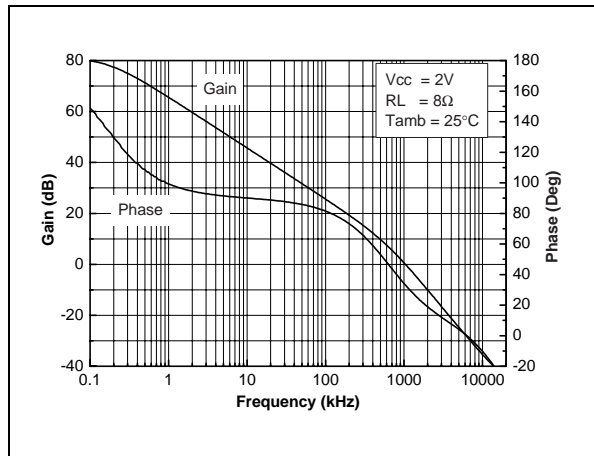
## Index of Graphs

Description	Figure	Page
Open Loop Gain	1 to 10	8, 9
Phase and Gain Margin vs Power Supply Voltage	11 to 20	9 to 11
Output Power vs Power Supply Voltage	21 to 23	11
Output Power vs Load Resistance	23 to 27	11, 12
Power Dissipation vs Output Power	28 to 31	12, 13
Power Derating Curves	32	13
Current Consumption vs Power Supply Voltage	33	13
PSRR vs Frequency	34	13
THD + N vs Output Power	35 to 49	13 to 16
THD + N vs Frequency	50 to 54	16
Signal to Noise Ratio vs Power Supply Voltage	55 to 58	17
Equivalent Input Noise voltage vs Frequency	59	17
Output Voltage Swing vs Supply Voltage	60	17
Crosstalk vs Frequency	61 to 65	18
Lower Cut Off Frequency Curves	66, 67	18, 19
Statistical Results on THD+N	68 to 79	19 to 21

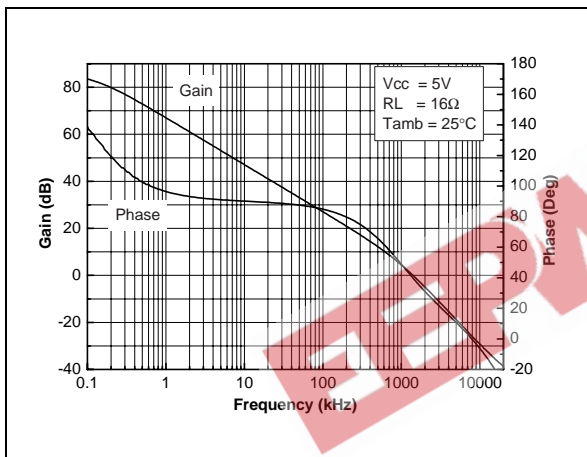
**Fig. 1 : Open Loop Gain and Phase vs Frequency**



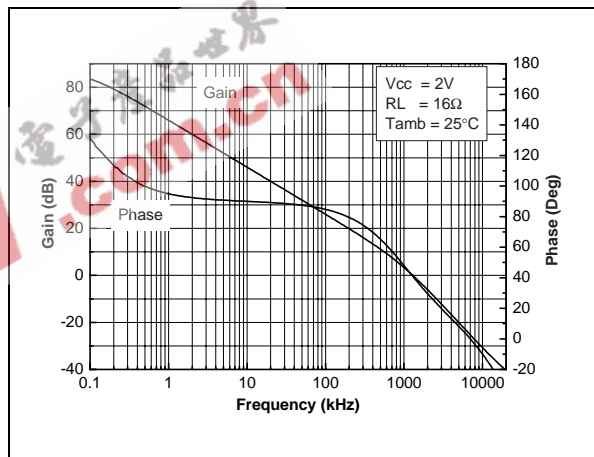
**Fig. 2 : Open Loop Gain and Phase vs Frequency**



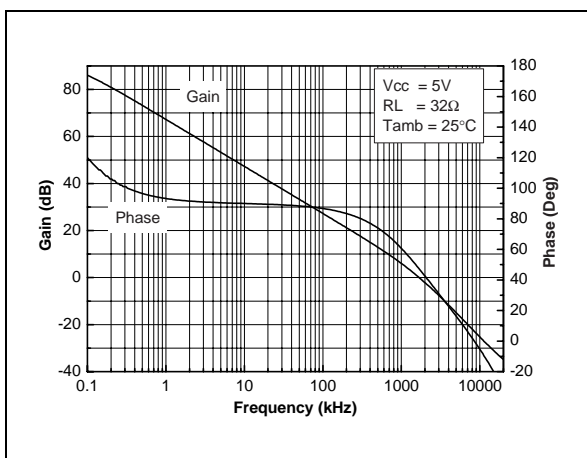
**Fig. 3 : Open Loop Gain and Phase vs Frequency**



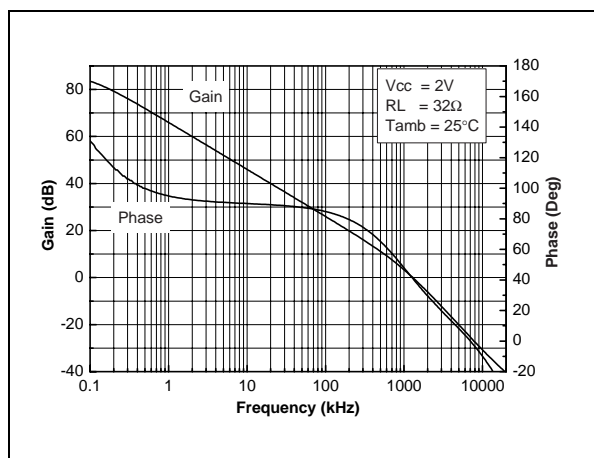
**Fig. 4 : Open Loop Gain and Phase vs Frequency**



**Fig. 5 : Open Loop Gain and Phase vs Frequency**

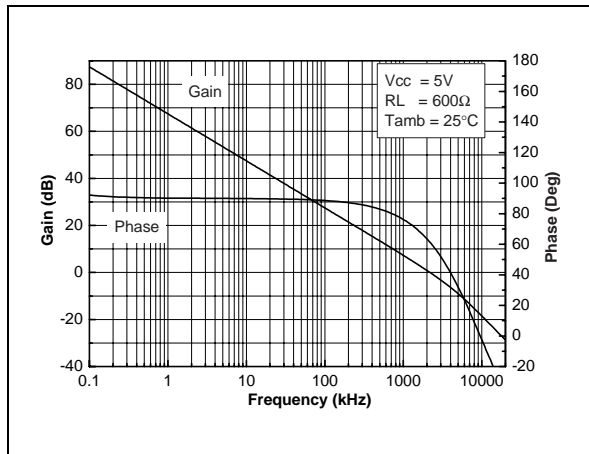


**Fig. 6 : Open Loop Gain and Phase vs Frequency**

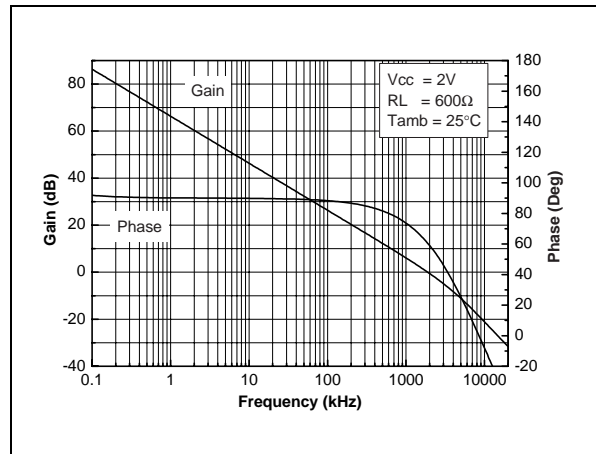




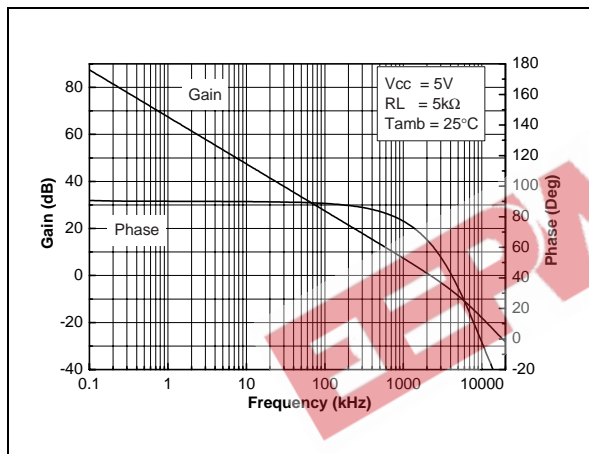
**Fig. 7 : Open Loop Gain and Phase vs Frequency**



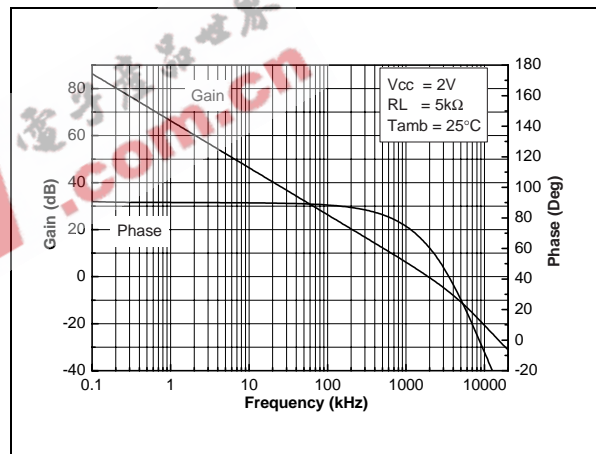
**Fig. 8 : Open Loop Gain and Phase vs Frequency**



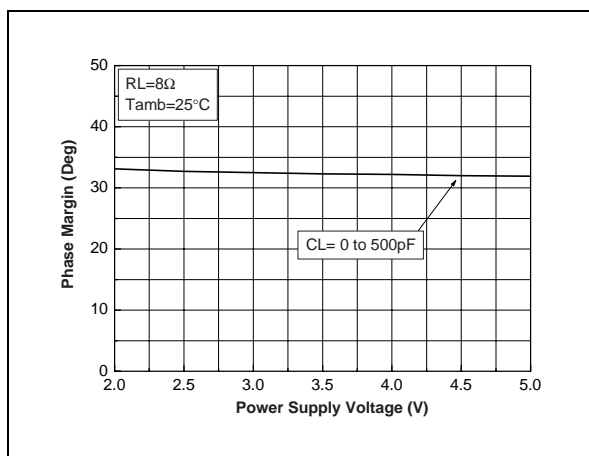
**Fig. 9 : Open Loop Gain and Phase vs Frequency**



**Fig. 10 : Open Loop Gain and Phase vs Frequency**



**Fig. 11 : Phase Margin vs Power Supply Voltage**



**Fig. 12 : Gain Margin vs Power Supply Voltage**

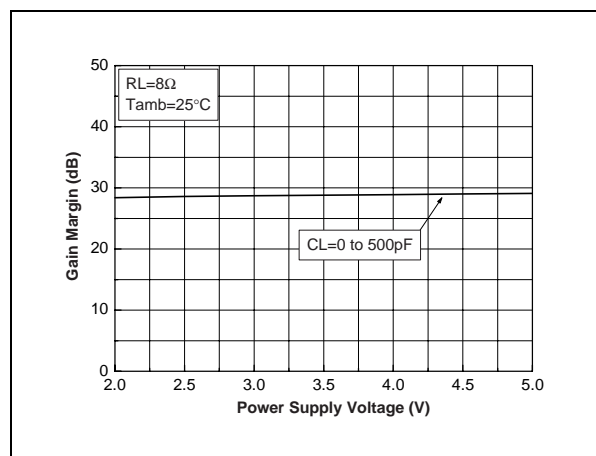


Fig. 13 : Phase Margin vs Power Supply Voltage

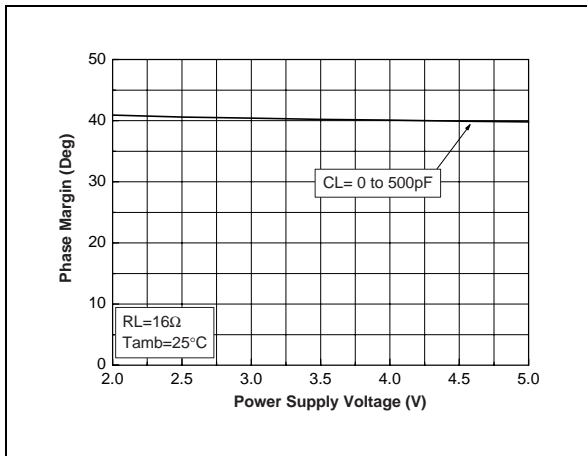


Fig. 14 : Gain Margin vs Power Supply Voltage

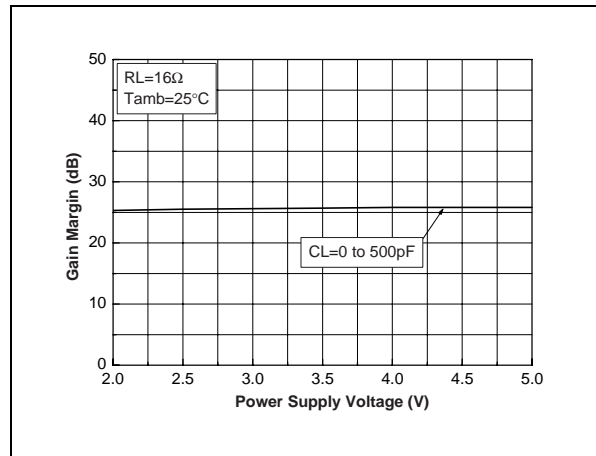


Fig. 15 : Phase Margin vs Power Supply Voltage

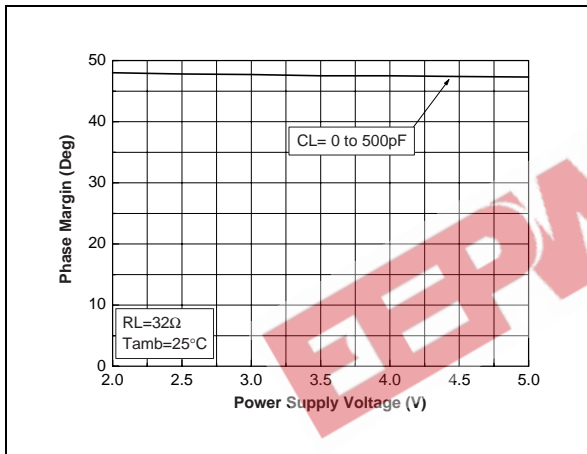


Fig. 16 : Gain Margin vs Power Supply Voltage

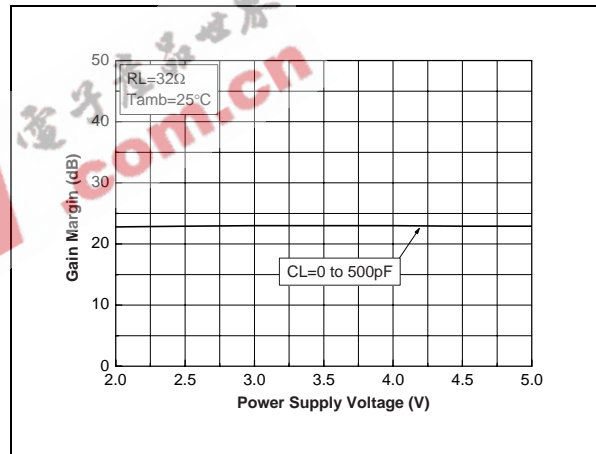


Fig. 17 : Phase Margin vs Power Supply Voltage

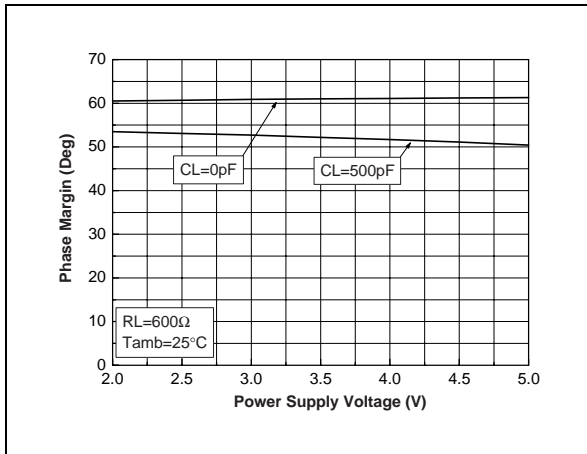


Fig. 18 : Gain Margin vs Power Supply Voltage

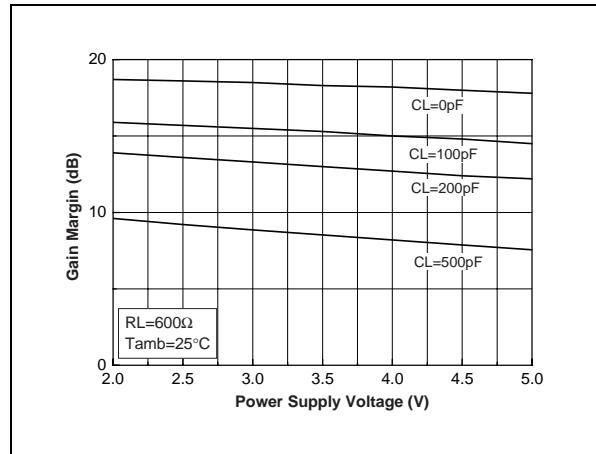


Fig. 19 : Phase Margin vs Power Supply Voltage

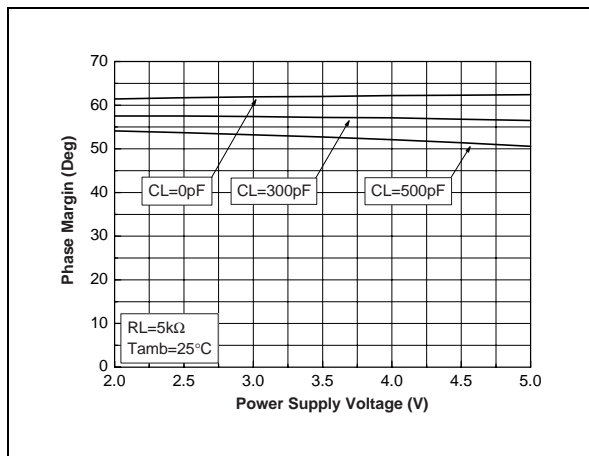


Fig. 20 : Gain Margin vs Power Supply Voltage

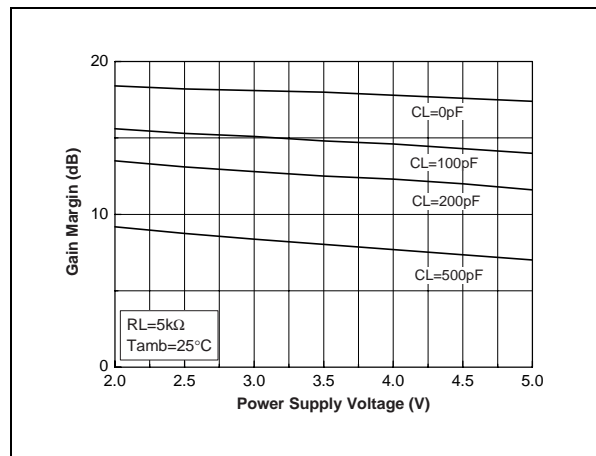


Fig. 21 : Output Power vs Power Supply Voltage

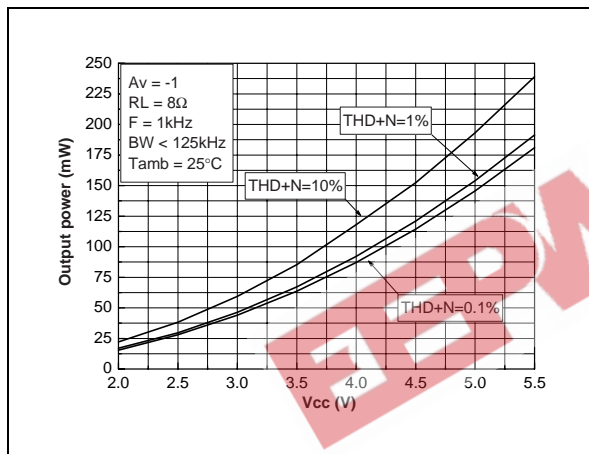


Fig. 22 : Output Power vs Power Supply Voltage

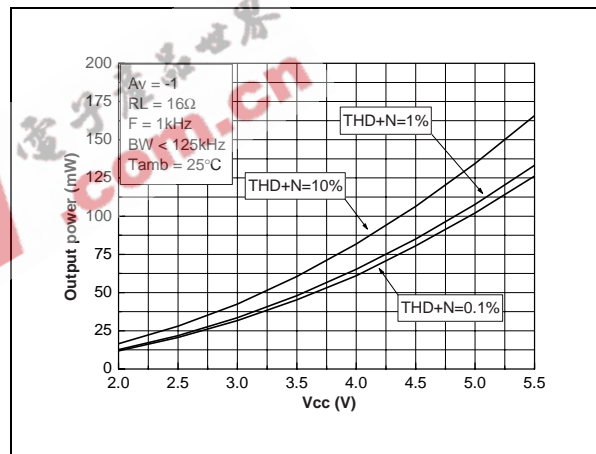


Fig. 23 : Output Power vs Power Supply Voltage

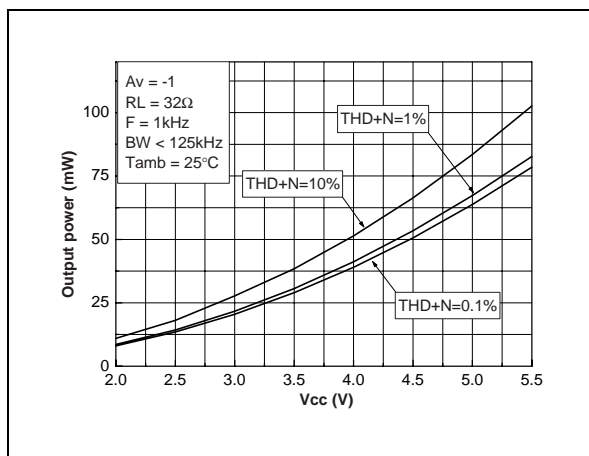


Fig. 24 : Output Power vs Load Resistance

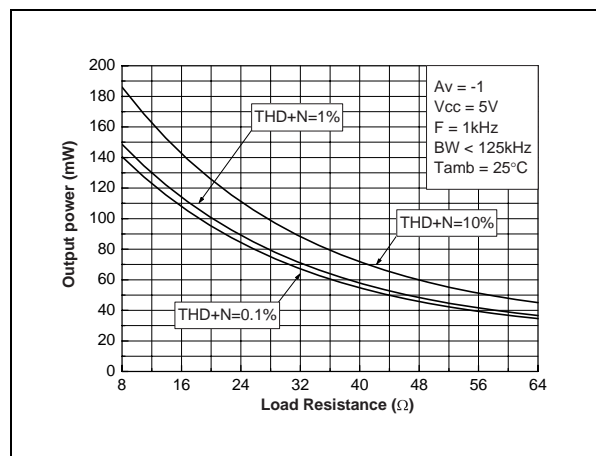


Fig. 25 : Output Power vs Load Resistance

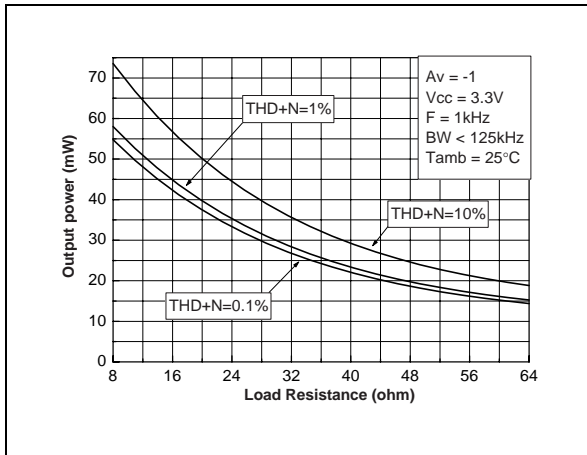


Fig. 26 : Output Power vs Load Resistance

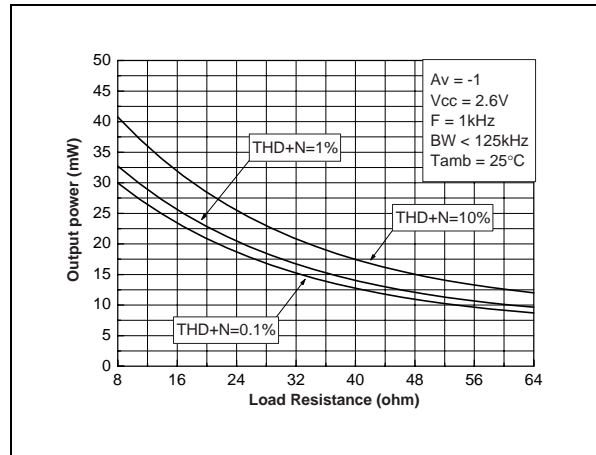


Fig. 27 : Output Power vs Load Resistance

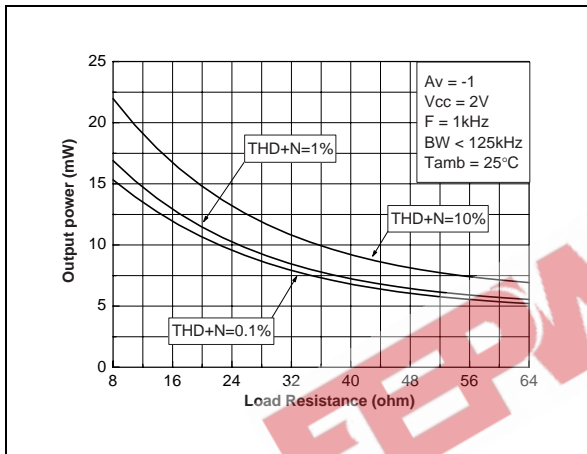


Fig. 28 : Power Dissipation vs Output Power

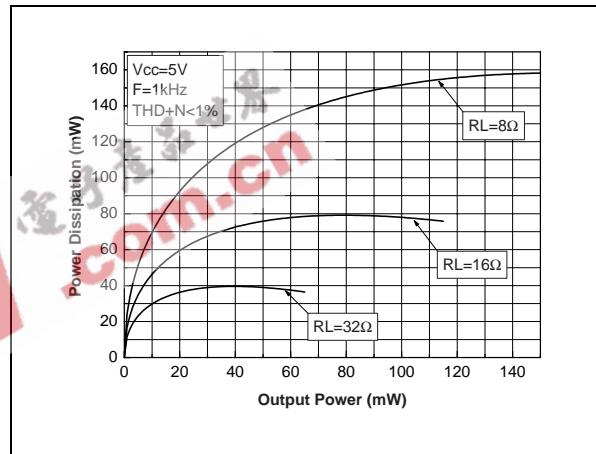


Fig. 29 : Power Dissipation vs Output Power

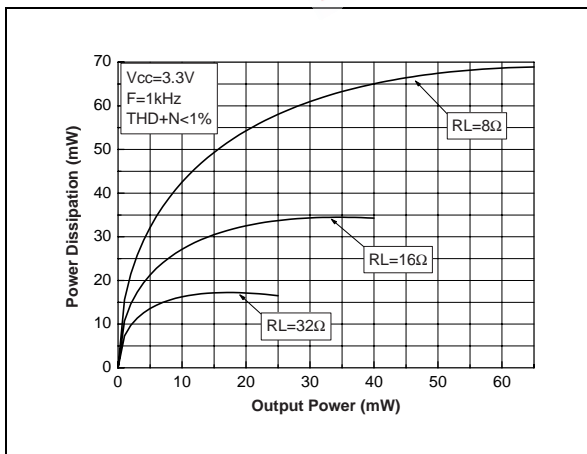


Fig. 30 : Power Dissipation vs Output Power

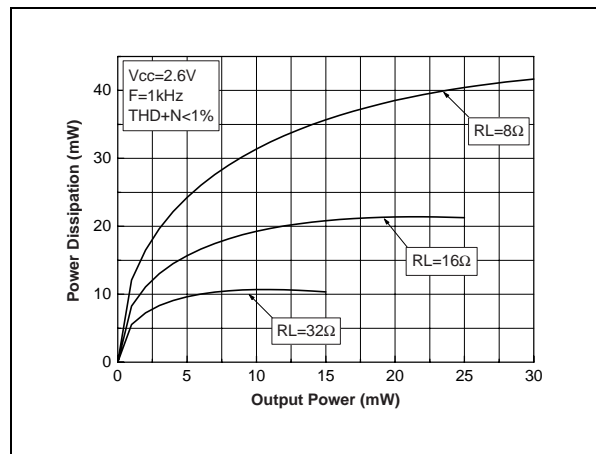


Fig. 31 : Power Dissipation vs Output Power

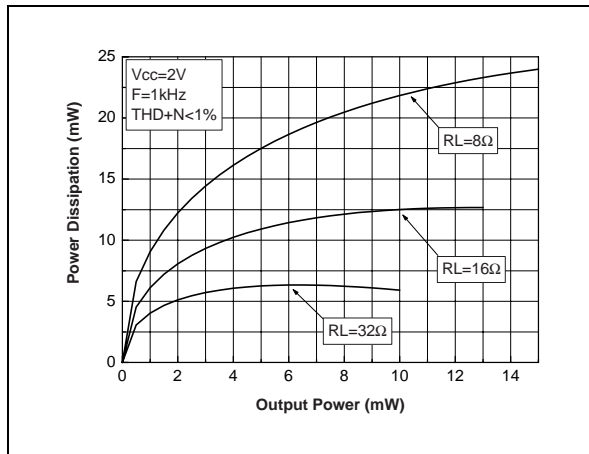


Fig. 32 : Power Derating vs Ambient Temperature

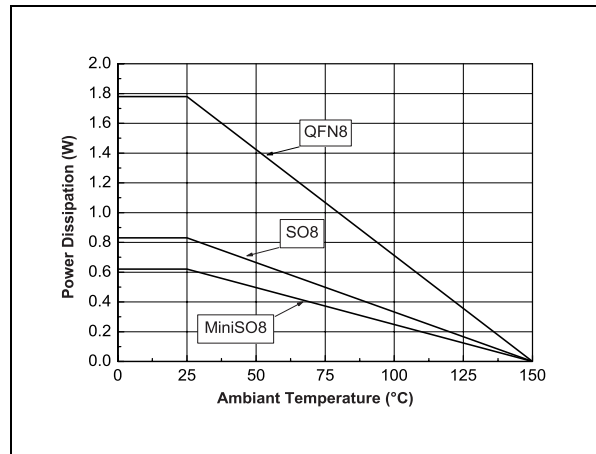


Fig. 33 : Current Consumption vs Power Supply Voltage

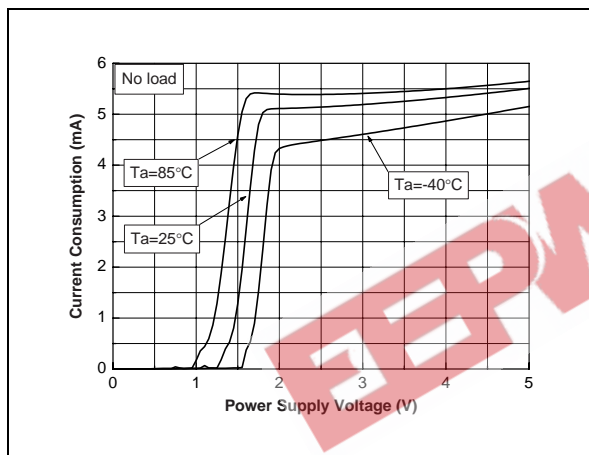


Fig. 34 : Power Supply Rejection Ratio vs Frequency

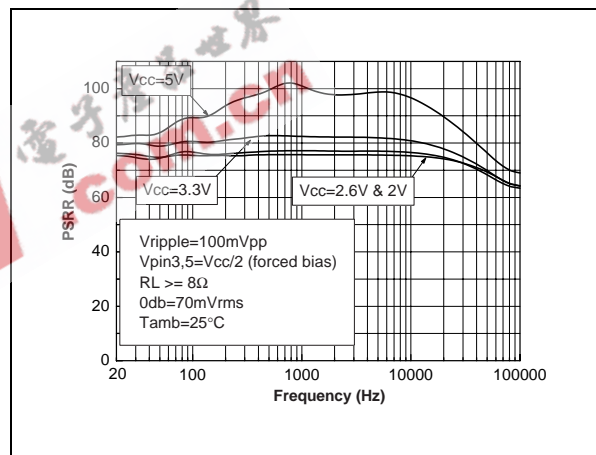


Fig. 35 : THD + N vs Output Power

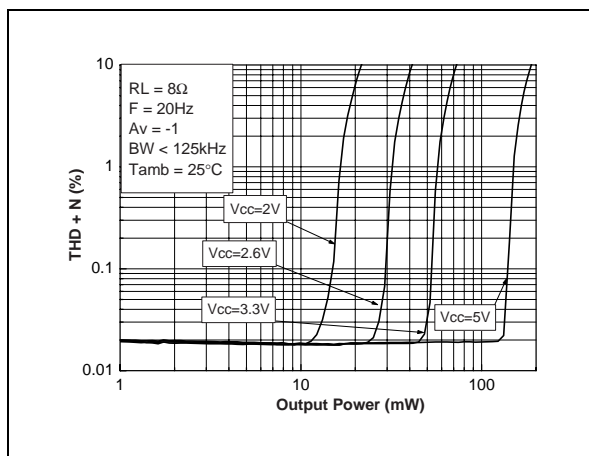


Fig. 36 : THD + N vs Output Power

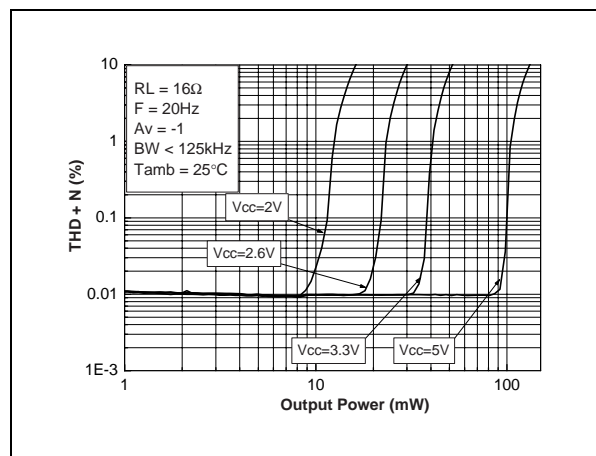


Fig. 37 : THD + N vs Output Power

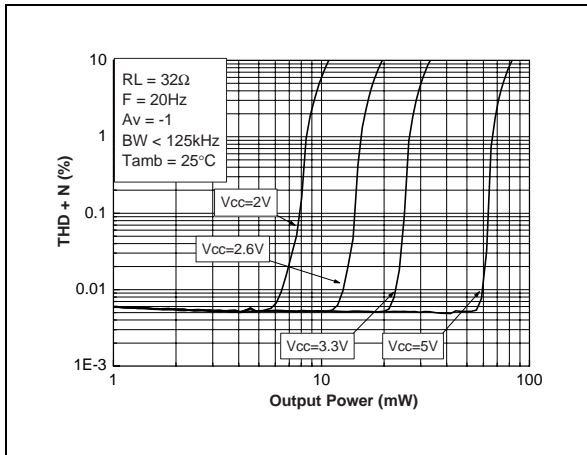


Fig. 38 : THD + N vs Output Power

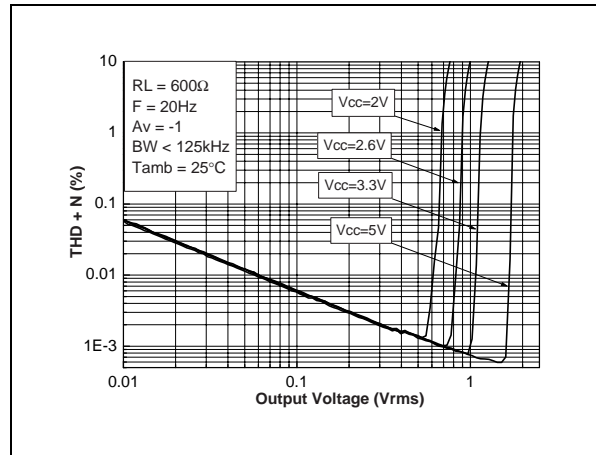


Fig. 39 : THD + N vs Output Power

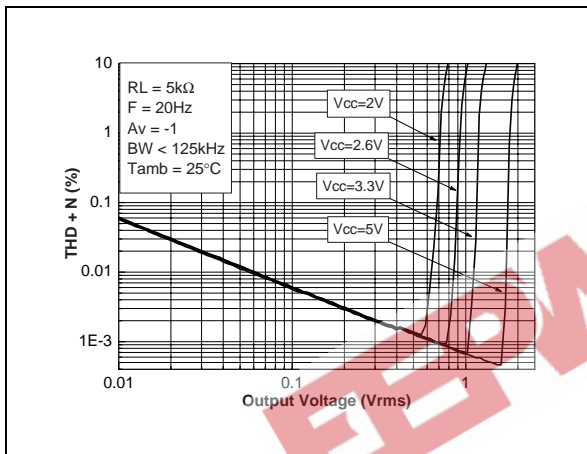


Fig. 40 : THD + N vs Output Power

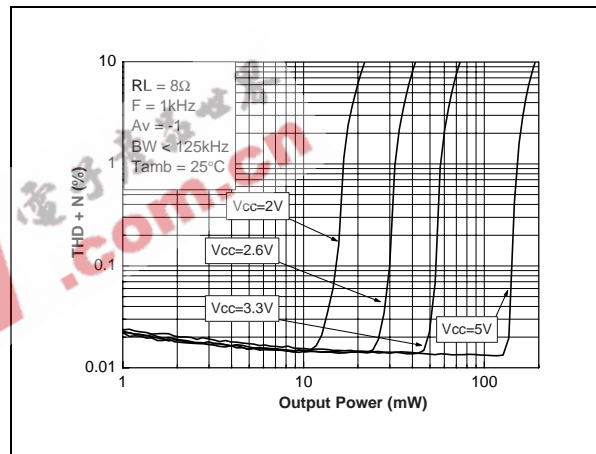


Fig. 41 : THD + N vs Output Power

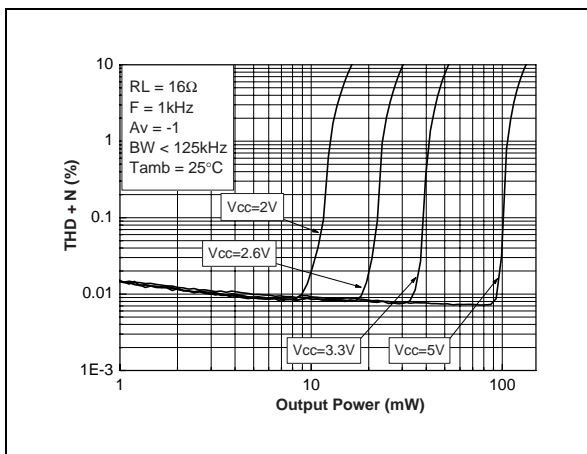


Fig. 42 : THD + N vs Output Power

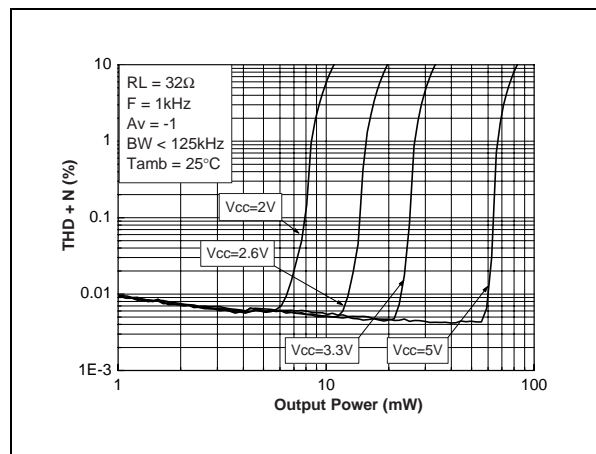


Fig. 43 : THD + N vs Output Power

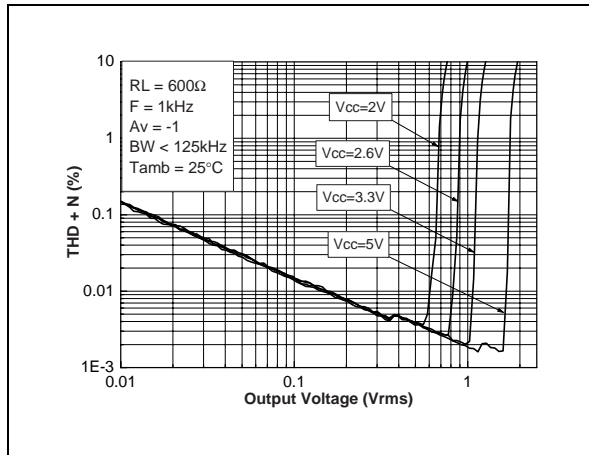


Fig. 44 : THD + N vs Output Power

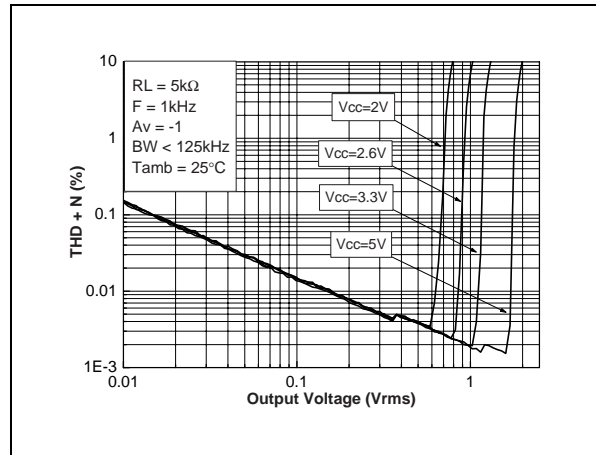


Fig. 45 : THD + N vs Output Power

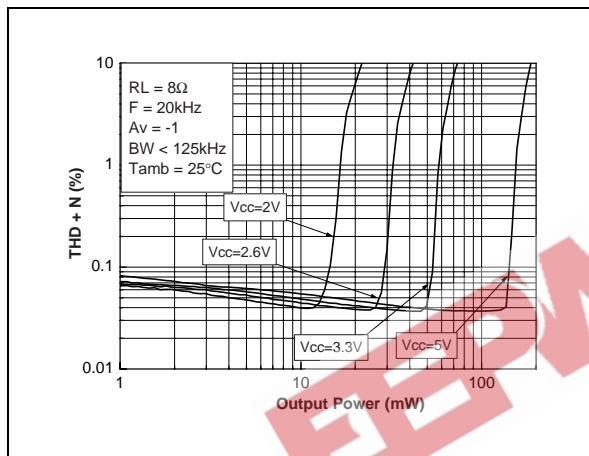


Fig. 46 : THD + N vs Output Power

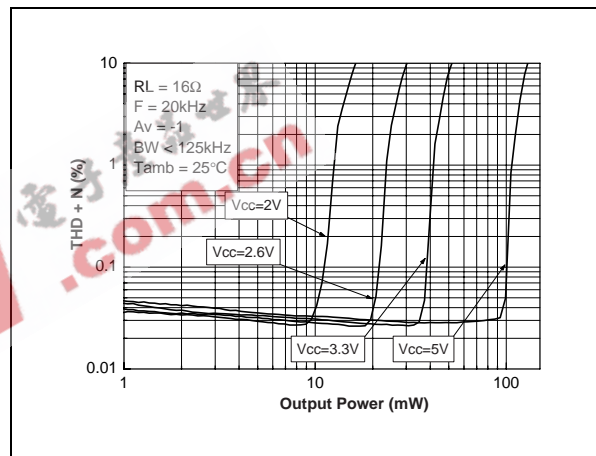


Fig. 47 : THD + N vs Output Power

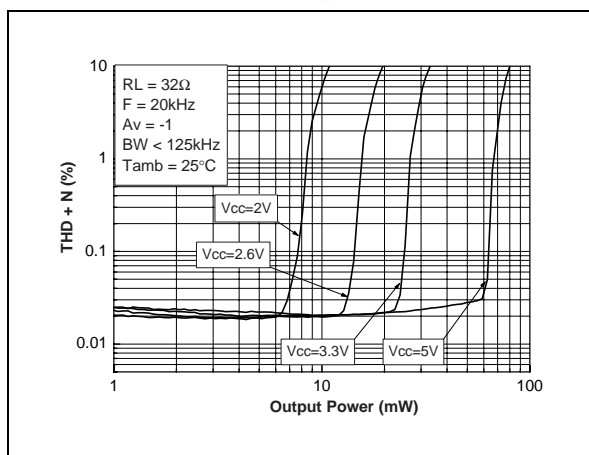


Fig. 48 : THD + N vs Output Power

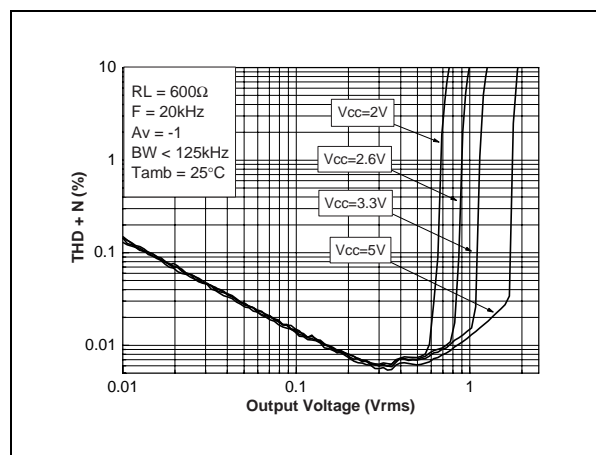


Fig. 49 : THD + N vs Output Power

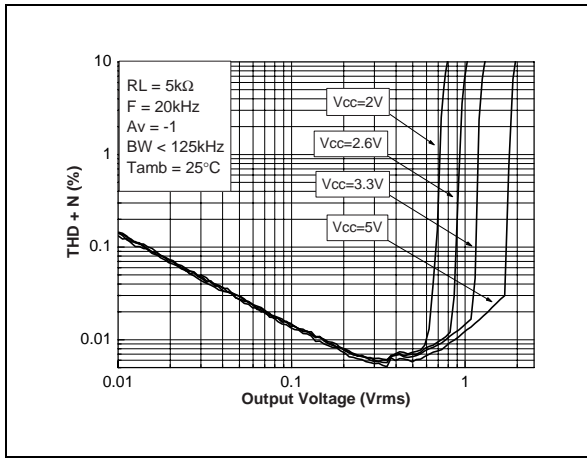


Fig. 50 : THD + N vs Frequency

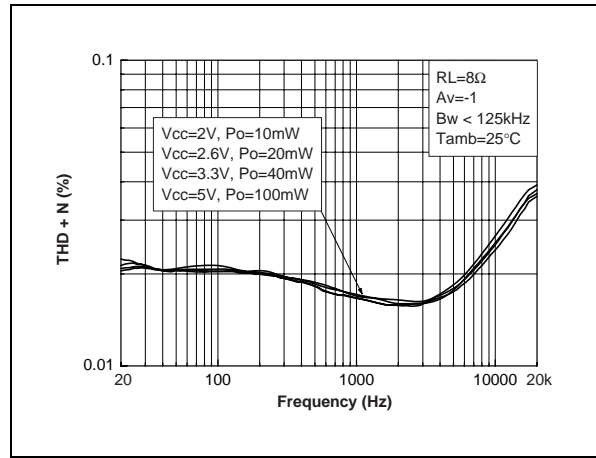


Fig. 51 : THD + N vs Frequency

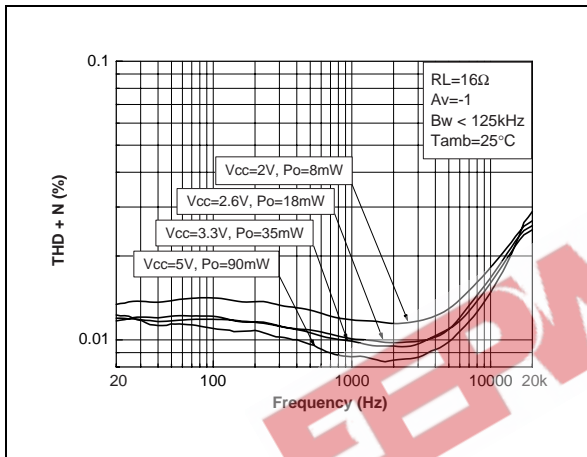


Fig. 52 : THD + N vs Frequency

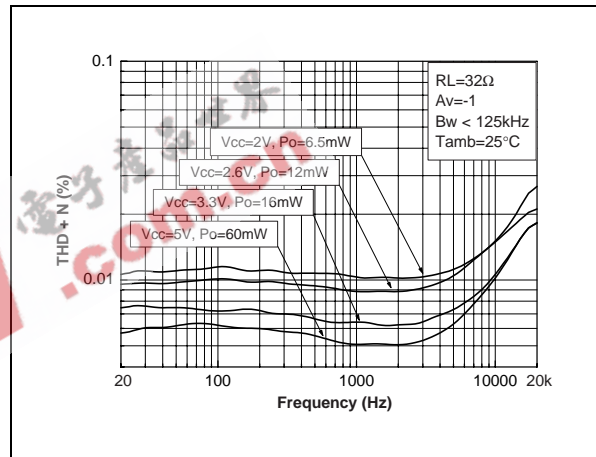


Fig. 53 : THD + N vs Frequency

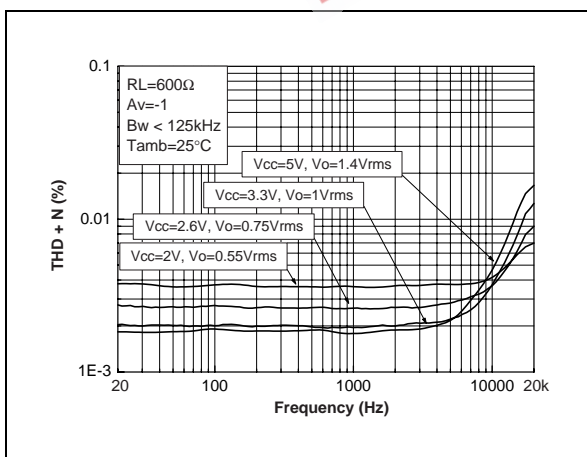
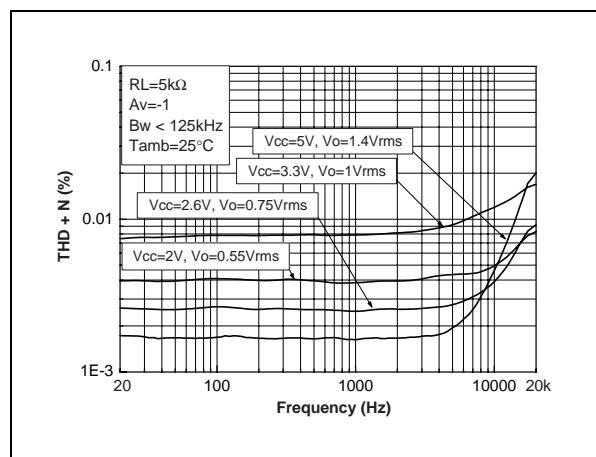
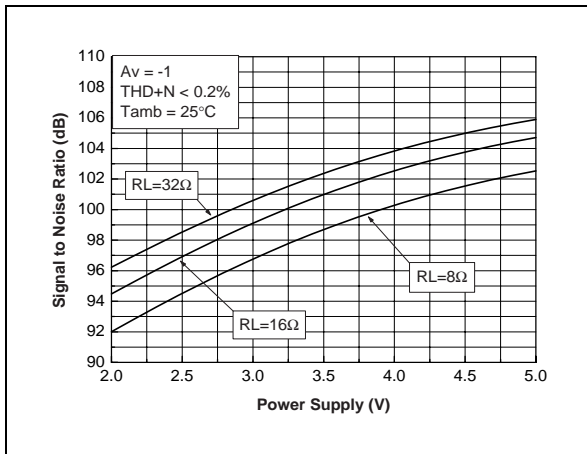


Fig. 54 : THD + N vs Frequency

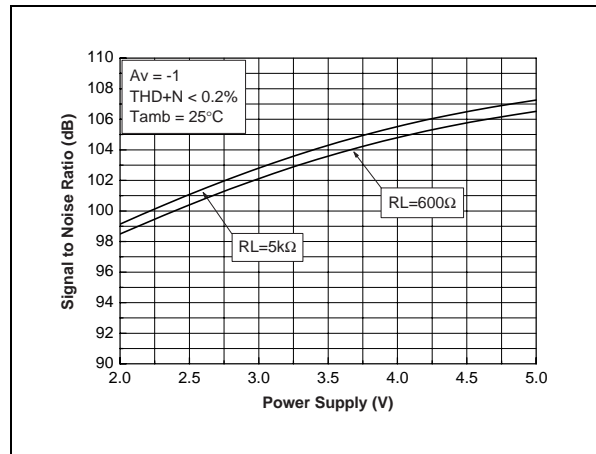




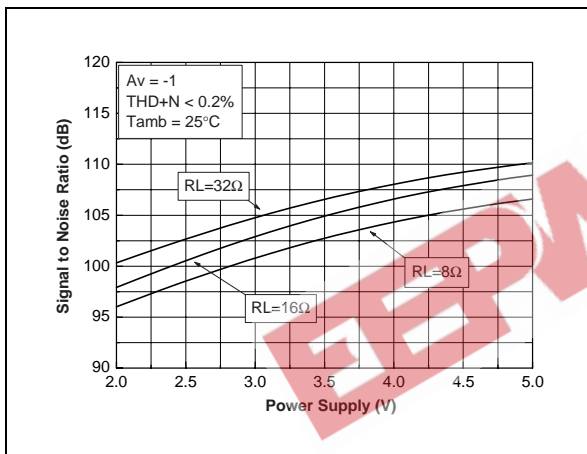
**Fig. 55 : Signal to Noise Ratio vs Power Supply Voltage with Unweighted Filter (20Hz to 20kHz)**



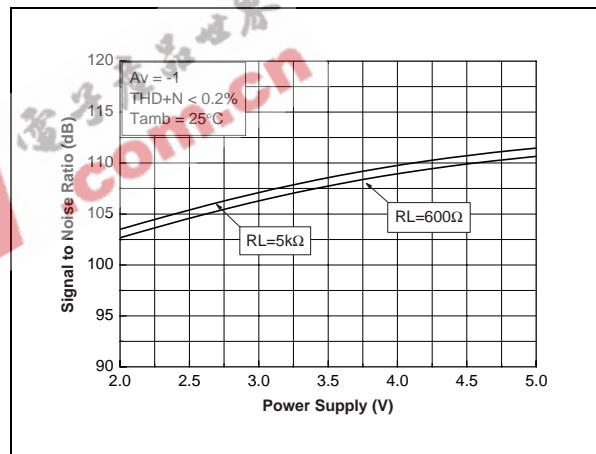
**Fig. 56 : Signal to Noise Ratio vs Power Supply Voltage with Unweighted Filter (20Hz to 20kHz)**



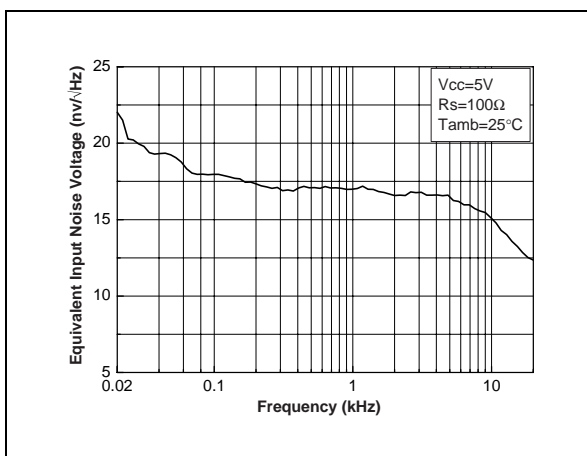
**Fig. 57 : Signal to Noise Ratio vs Power Supply Voltage with Weighted Filter Type A**



**Fig. 58 : Signal to Noise Ratio vs Power Supply Voltage with Weighted Filter Type A**



**Fig. 59 : Equivalent Input Noise Voltage vs Frequency**



**Fig. 60 : Output Voltage Swing vs Power Supply Voltage**

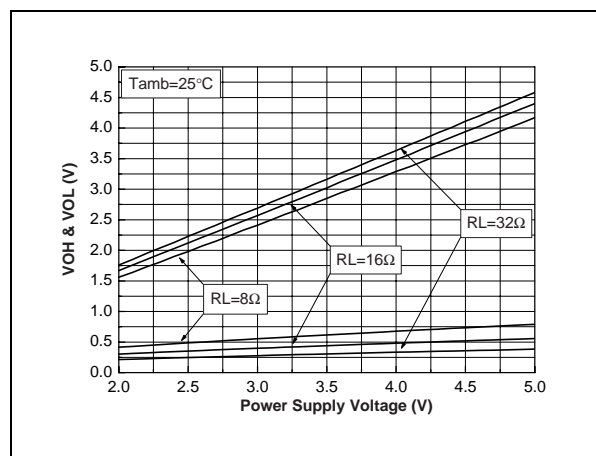


Fig. 61 : Crosstalk vs Frequency

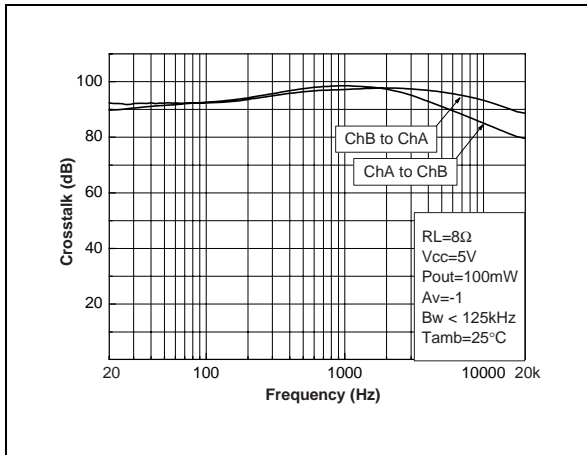


Fig. 62 : Crosstalk vs Frequency

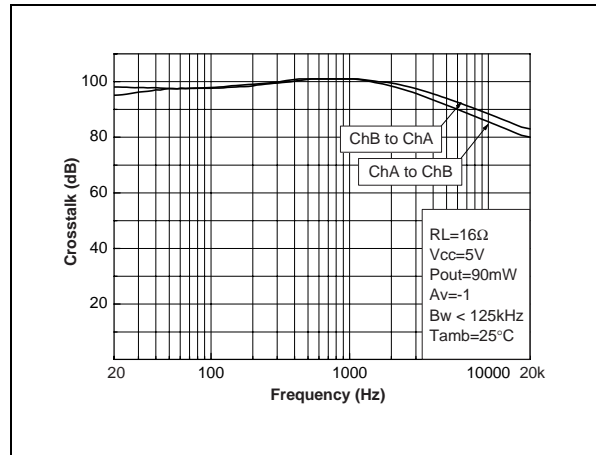


Fig. 63 : Crosstalk vs Frequency

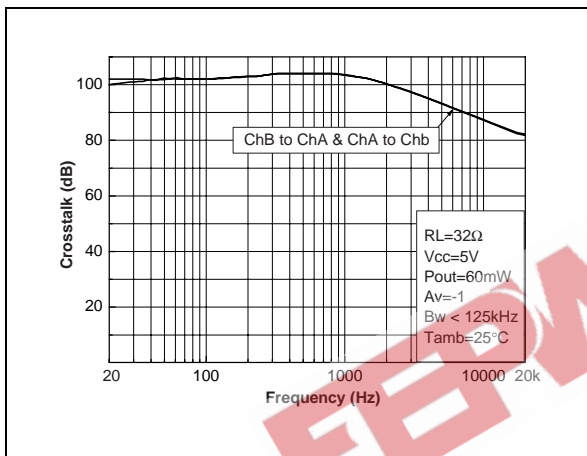


Fig. 64 : Crosstalk vs Frequency

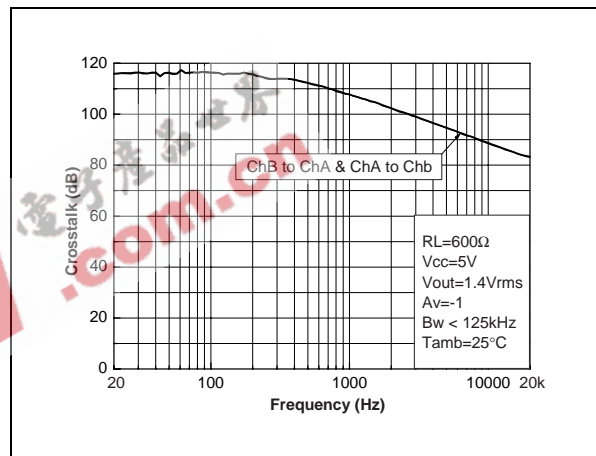


Fig. 65 : Crosstalk vs Frequency

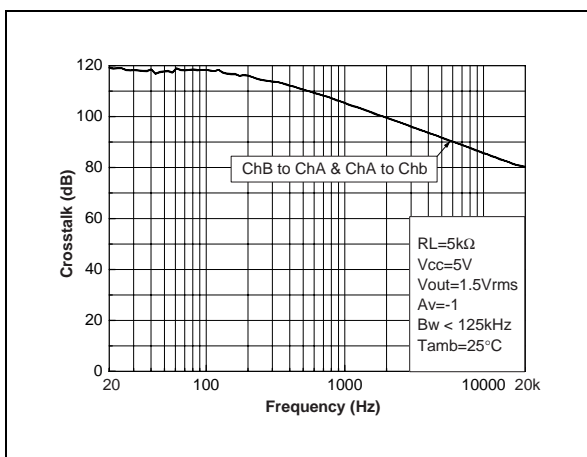


Fig. 66 : Lower Cut Off Frequency vs Output Capacitor

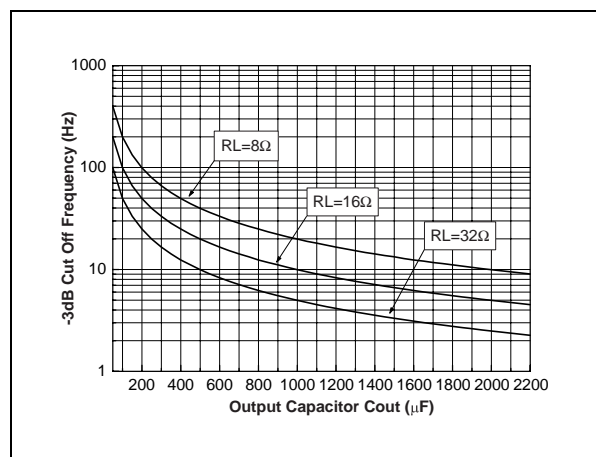


Fig. 67 : Lower Cut Off Frequency vs Input Capacitor

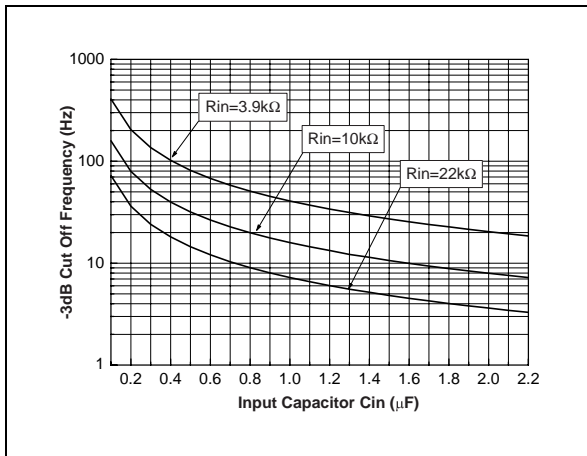


Fig. 69 : Best Case Distribution of THD+N

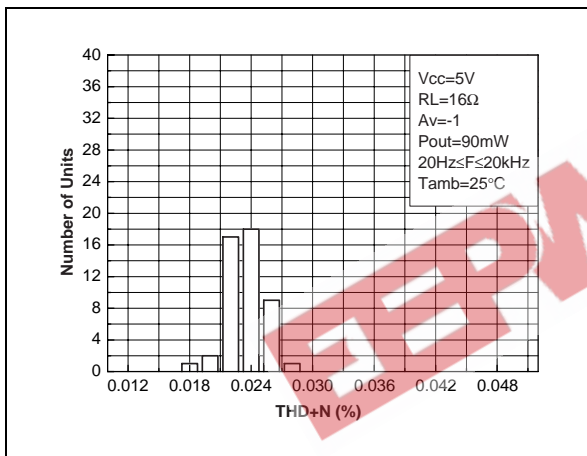


Fig. 71 : Typical Distribution of THD+N

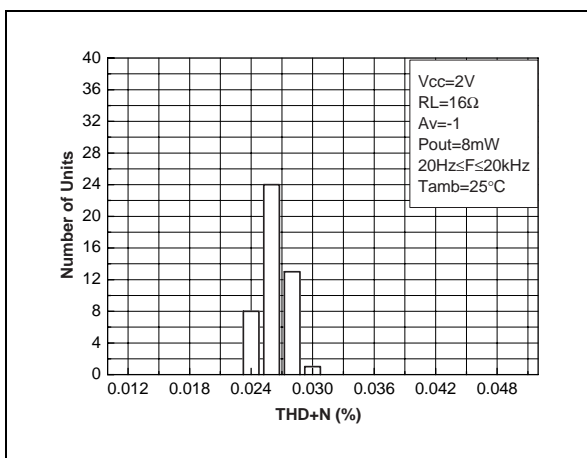


Fig. 68 : Typical Distribution of THD+N

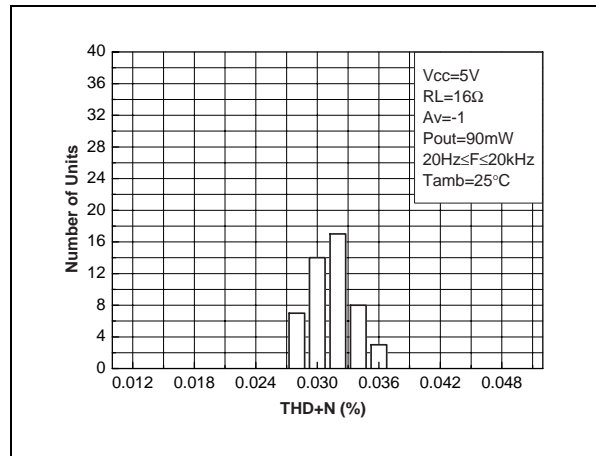


Fig. 70 : Worst Case Distribution of THD+N

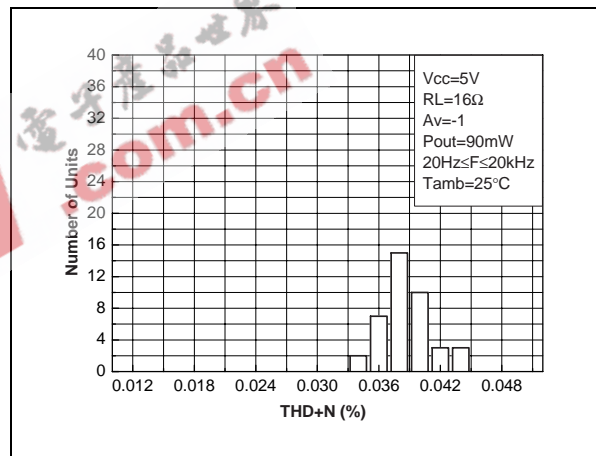


Fig. 72 : Best Case Distribution of THD+N

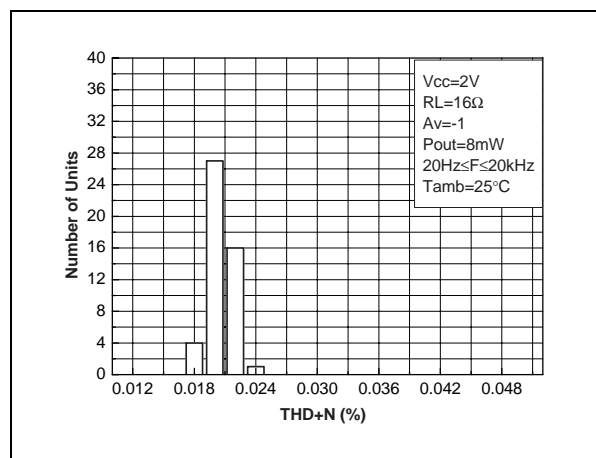


Fig. 73 : Worst Case Distribution of THD+N

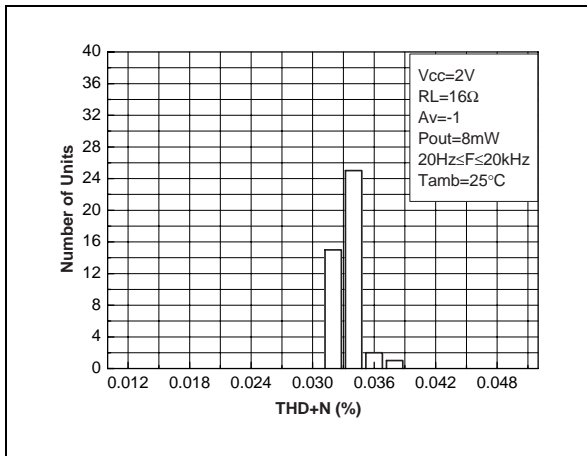


Fig. 74 : Typical Distribution of THD+N

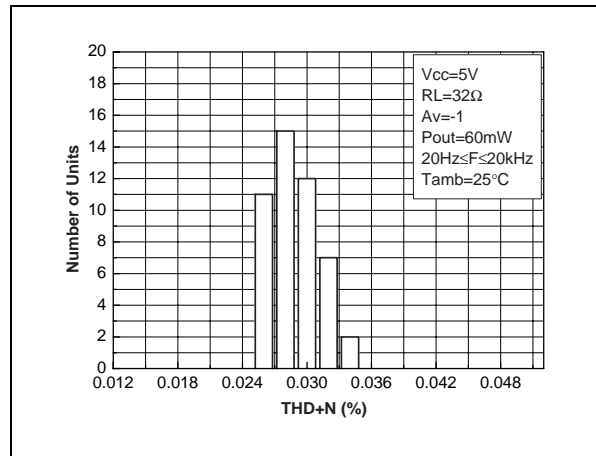


Fig. 75 : Best Case Distribution of THD+N

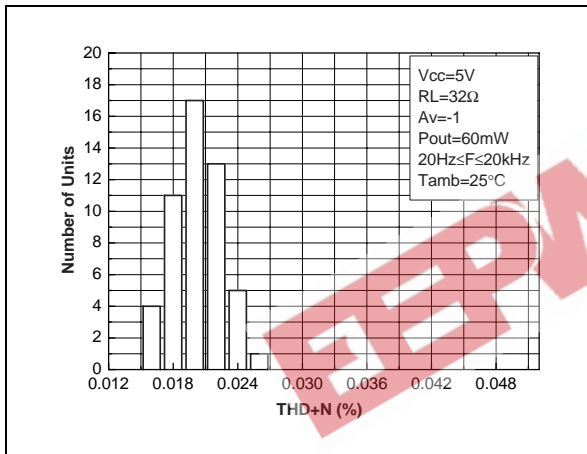


Fig. 76 : Worst Case Distribution of THD+N

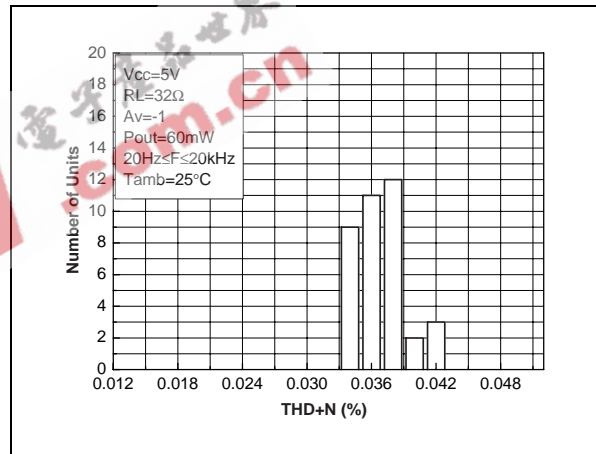


Fig. 77 : Typical Distribution of THD+N

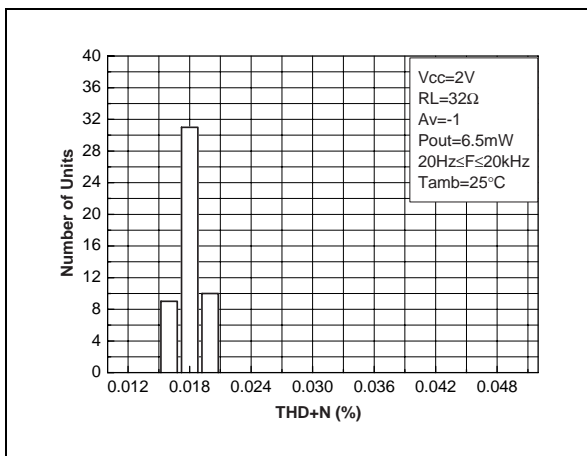


Fig. 78 : Best Case Distribution of THD+N

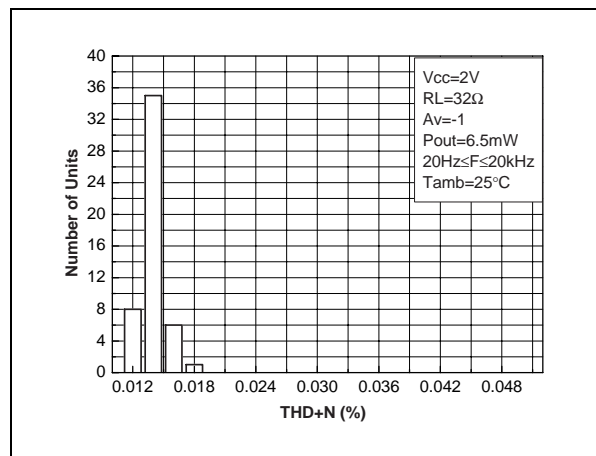
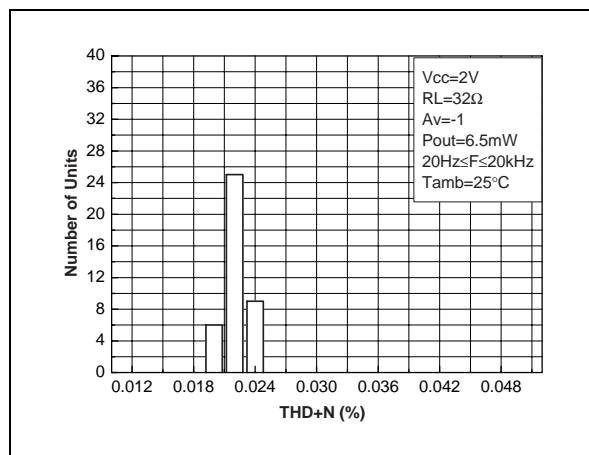


Fig. 79 : Worst Case Distribution of THD+N

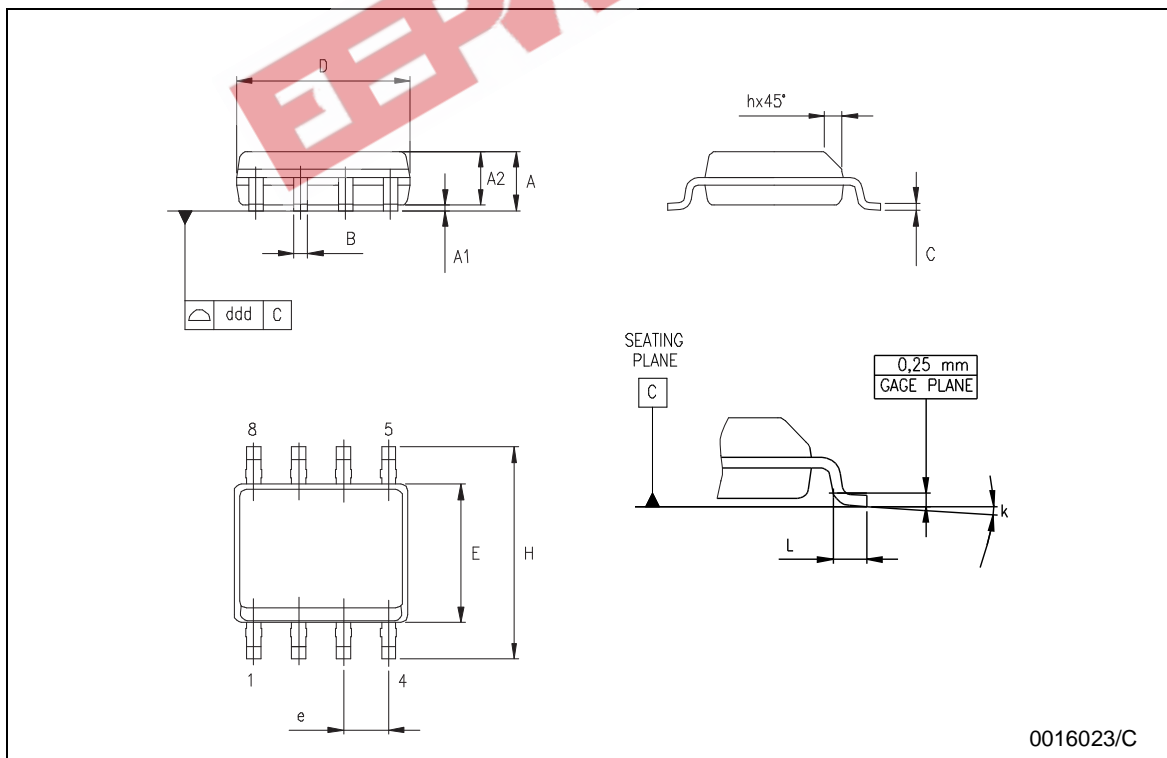


EEPW 电子产品世界  
.com.cn

PACKAGE MECHANICAL DATA

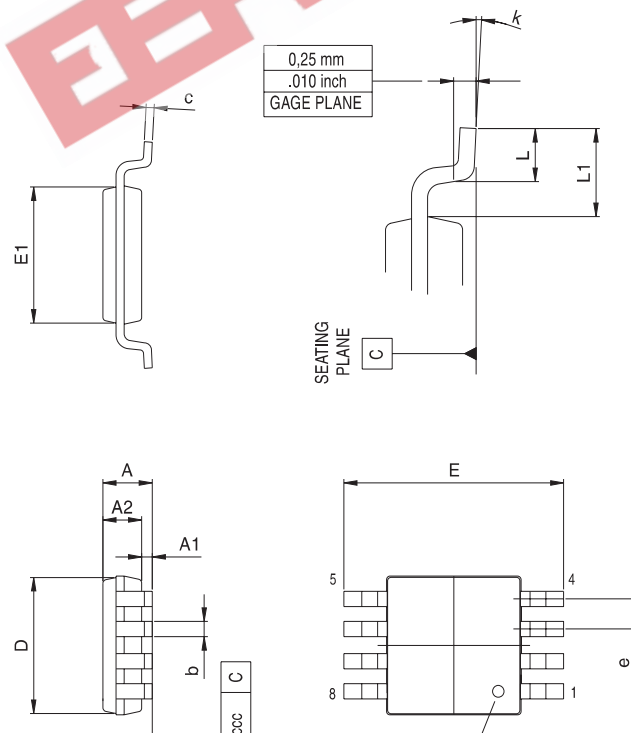
**SO-8 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.04		0.010
A2	1.10		1.65	0.043		0.065
B	0.33		0.51	0.013		0.020
C	0.19		0.25	0.007		0.010
D	4.80		5.00	0.189		0.197
E	3.80		4.00	0.150		0.157
e		1.27			0.050	
H	5.80		6.20	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	8° (max.)					
ddd			0.1			0.04



**PACKAGE MECHANICAL DATA**

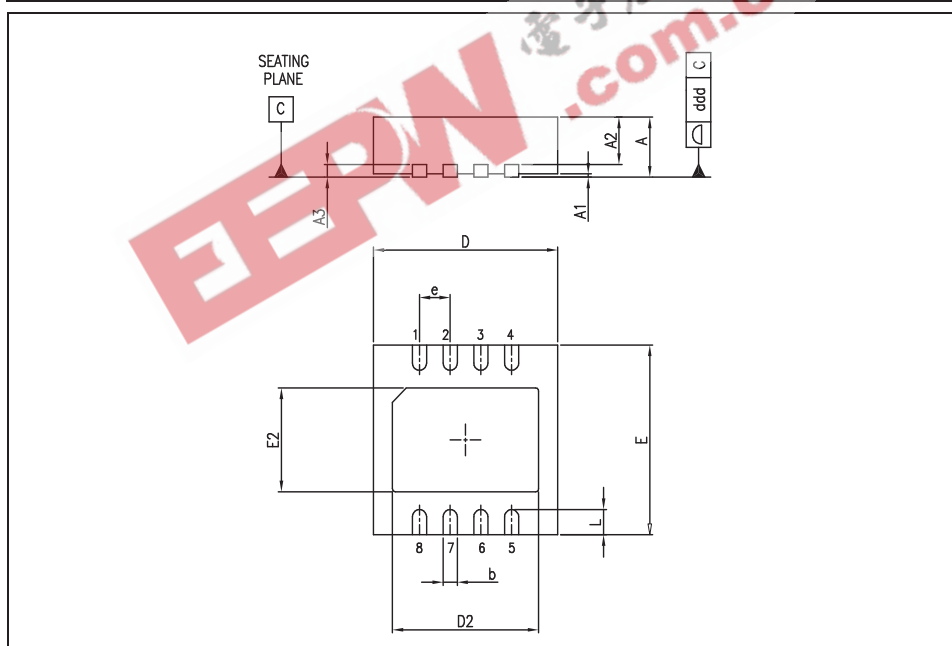
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.1			0.043
A1	0.05	0.10	0.15	0.002	0.004	0.006
A2	0.78	0.86	0.94	0.031	0.031	0.037
b	0.25	0.33	0.40	0.010	0.13	0.013
c	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
E	4.75	4.90	5.05	0.187	0.193	0.199
E1	2.90	3.00	3.10	.0114	0.118	0.122
e		0.65			0.026	
K	0°		6°	0°		6°
L	0.40	0.55	0.70	0.016	0.022	0.028
L1			0.10			0.004



PACKAGE MECHANICAL DATA

DFN8 (3x3) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.80	0.90	1.00	31.5	35.4	39.4
A1		0.02	0.05		0.8	2.0
A2		0.70			27.6	
A3		0.20			7.9	
b	0.18	0.23	0.30	7.1	9.1	11.8
D		3.00			118.1	
D2	2.23	2.38	2.48	87.8	93.7	97.7
E		3.00			118.1	
E2	1.49	1.64	1.74	58.7	64.6	68.5
e		0.50			19.7	
L	0.30	0.40	0.50	11.8	15.7	19.7



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All Rights Reserved  
 STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia